

c) Amendments to the Claims:

Please amend the claims as follows. A detailed listing of all the claims that are or were in the application is provided.

--1. (Presently amended) A sputtering method for forming a film on a substrate in a film forming space while monitoring emission intensity of plasma, the method comprising the steps of:

detecting a thickness of the film formed on said substrate;

comparing a detected value with a preset value of the film thickness;

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deciding a target value of the emission intensity that will provide the preset value of the film thickness in accordance with a compared result; and

adjusting the emission intensity to the target value.

2. (Presently amended) ~~A~~ The sputtering method according to Claim 1, ~~wherein further comprising controlling~~ a flow rate of at least one ~~of gases~~ gas introduced into said film forming space, thereby adjusting the ~~is controlled such that actual~~ emission intensity ~~is adjusted at~~ to the target value of the emission intensity.

3. (Presently amended) ~~A~~ The sputtering method according to Claim 1, wherein a target containing In is employed as a sputtering target.

4. (Presently amended) ~~A~~ The sputtering method according to Claim 1, wherein a cylindrical rotating target is employed as a sputtering target.

5. (Presently amended) ~~A~~ The sputtering method according to Claim 2, wherein ~~an~~ oxygen gas is selected as ~~one of the gases, of the gas for which~~ the flow rate is controlled.

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6. (Presently amended) ~~A~~ The sputtering method according to Claim 1, wherein the target value of the emission intensity is set to fall in a predetermined range defined beforehand.

7. (Presently amended) ~~A~~ The sputtering method according to Claim 6, wherein if the target value deviates from said predetermined range, sputtering is stopped.

8. (Presently Amended) A sputtering apparatus comprising a film forming container, a substrate feeding mechanism, and an emission intensity monitor, the apparatus further comprising:

a film thickness measuring device, configured to measure ~~for measuring~~ a thickness of a film formed on a substrate and outputting a measured result; ~~and~~

a comparator, configured to compare ~~for comparing~~ an output of said film thickness measuring device with a preset value of the film thickness and to output ~~outputting~~ a target value of said emission intensity monitor in accordance with a compared result; and

an emission intensity target-value setting unit, configured to receive the output target value from the comparator, and to adjust the emission intensity to the target value.

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9. (Presently amended) ~~A~~ The sputtering apparatus according to Claim 8, further comprising wherein the emission intensity target-value setting unit comprises a gas flow rate control mechanism for receiving the target value of said emission intensity monitor and controlling a flow rate of at least one of gases introduced to said film forming container in accordance with the target value.
